

POWER DISCRETES & MODULES

- ▶ Voltage & Current Regulation Diodes

▶ Small Signal Diodes and Diode Arrays

▶ IGBT

▶ Power MOSFET

▶ Silicon Carbide (SiC) Semiconductor

▶ Power Modules

▶ JFET

▶ BJT (BiPolar Junction Transistor)

- BJT Modules (Power Integrated Circuit, PIC)

- Darlington Transistors

- Darlington Transistor Array

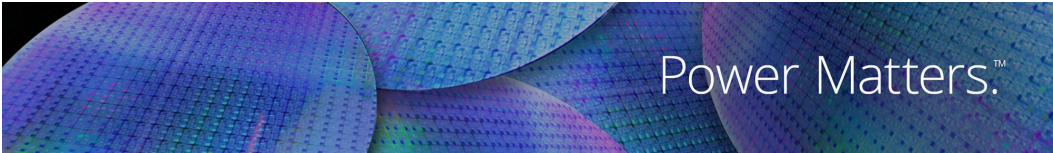
- NPN PNP Complimentary Transistor

- **NPN Transistor**

- PNP Transistor

▶ Legacy Power Discretes & Modules

▶ Diode and Rectifier Devices



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Power Discretes & Modules

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BJT (BiPolar Junction Transistor)

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NPN Transistor

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JAN2N1481 (#52526)

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Product Status

In Production

Overview

Resources

Diagrams

Ordering

Support

This family of 2N1479 through 2N1482 medium-power, planar transistors is military qualified to the JAN level for high-reliability applications.

PackageESD Bag

Carrier:

Electrical Rating	Symbol	Min	Typ	Max	Unit
DC Current Gain	HFE	35		100	
Turn Off Time (nS)	t _{off}			25000	ns

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Current (dc)	I _C			1.5	A
Collector to Base Voltage (Emitter Open)	V _{CBO}			60	V
Collector to Emitter Saturation Voltage	V _{CE(sat)}			0.75	V
Collector-Emitter Voltage (Base Open)	V _{CEO}			40	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			12	V
Junction Temperature (°C)	T _J	-65		200	°C
Power Dissipation	P _D			1	W
Thermal Resistance, Junction to Case (°C/W)	R _{θJC}			35	°C/W

Alphanumeric Parameter	Value
Quality Level	JAN

This part can be found in the following product categories:

- Power Discretes & Modules ▶ BJT (BiPolar Junction Transistor)

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